ECE321 – Electronics I

Lecture 1: Introduction to Digital Electronics

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Office hours: Tuesday 2:00-3:00PM or by appointment
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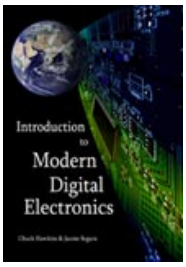
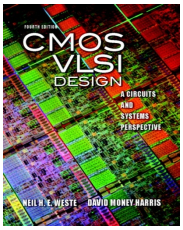
Textbook and Background

- **Main reference material is your notes in the class and the handouts**
- **Two equally important textbooks are:**
  - **Charles Hawkins and Jaume Segura, "Introduction to Modern Digital Electronics," 1st edition, SciTech Publishing, 2012, ISBN: 9781613530023**
  - **Neil Weste and David Harris, "CMOS VLSI Design: A Circuits and Systems Perspective," 4th Edition, Addison Wesley, March 11, 2010, ISBN-13: 978-0321547743**
- **Lecture Notes: combination of slides, homeworks and announcements**
  - **Slides will be posted on the class webpage**
  - **Class webpage: *www.ece.unm.edu/~payman/classes/ECE321***
  - **User Name: student**
  - **Password: electronics**

Textbooks and Outline





- Basic CMOS Transistor Modeling
- CMOS Inverter
- Delay and Power Calculations
- Interconnect Modeling
- Design Rules and Layout
- Design Tools
- CMOS Fabrication
- Combinational / Sequential Logic
- Static / Dynamic / Domino Logic
- Basic Timing Analysis
- Basic SRAM and DRAM Memories

Grading Policy

- Your grade in the course will be comprised of:
  - Homework (20%)
  - Class Contribution (5%)
  - Design Project (15%)
  - Tests (30%)
  - Final Exam (30%)
- There will be 2 midterm tests, but only 1 will be considered and the worst test will be ignored. Therefore, there is no makeup tests or exams.
- Final letter grade will be based on curve and class performance
- Your participation in class is very important
- Suggestions for success:
  - Participate in the class and ask questions
  - Read the textbook
  - Work on problems

Homework Policy

- Homework will be assigned for each Monday of the class. Please refer to the class website for the homework assignments.
- Homework due at the beginning of the lecture. No exception!
- Solutions will be posted on the class website as soon as it is available.
- Late homework and projects will not be accepted

Course Project

- There will be design project assigned including:
  - Layout design using L-Edit
  - Circuit extract and spice simulation
- The design problem will be a team project. However, the roles of each team member should be rotated during the course of the project.
- Project grade will be based on:
  - Quality of report
  - Performance (speed/delay)
  - Power dissipation
  - Layout area
- There will be a 10% extra credit for any design with minimum layout area, or maximum performance, or minimum power consumption

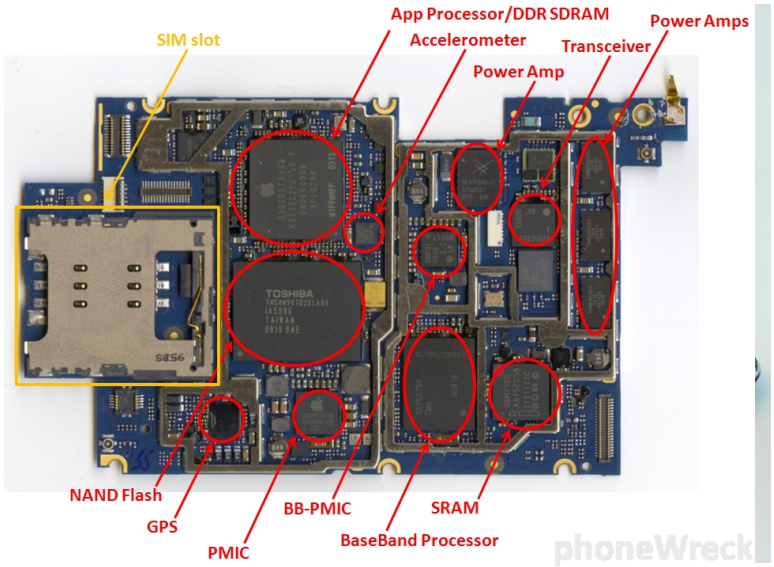
Course Objectives

- Analyze the basic device physics and predict the behavior of electrons and holes in a p-n junction
- Analyze multiple diode circuits with different types of diodes using the piecewise linear model and the small-signal equivalent circuit
- Analyze the operation of a field effect transistor and determine the DC/AC response of the FET
- Design and analyze the operation of the CMOS Inverter, NAND, NOR, and T-gates
- Determine the layout diagram for various logic gates
- Draw the fabrication steps for fabrication of logic gate circuits
- Understanding the concept of timing analysis, delay, and power estimations

Class Schedule

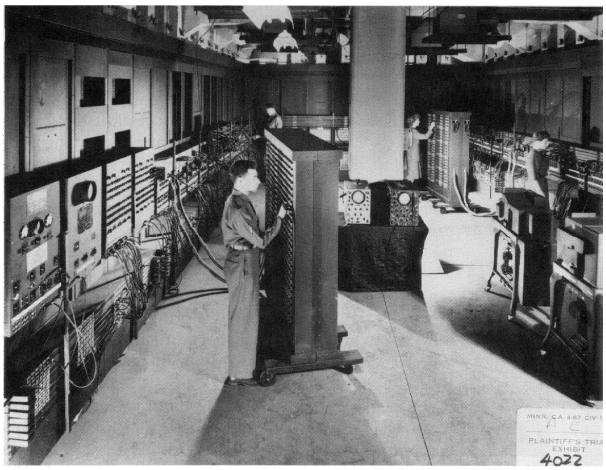
Date	Day	Topic	Reading/Coverage
August 20	Mon	Introduction to Digital Electronics	Handout
August 22	Wed	Basic Circuits with Diodes	1.1 - 1.8
August 27	Mon	Basic Solid State Physics	2.1 - 2.3
August 28	Wed	Physics of Semiconductor Diodes	2.4 - 2.6
September 03	Mon	Labor Day	-
September 05	Wed	Physics of Semiconductor MOSFETs	3.1
September 10	Mon	MOSFET I-V Characteristics	3.2
September 12	Wed	Basic Circuits with MOSFET	Handout
September 17	Mon	MOSFET Threshold Voltage & Parasitic Capacitance	Handout
September 19	Wed	MOSFET Scaling Issues	Handout
September 24	Mon	TEST	-
September 26	Wed	Basic Digital Circuits with MOSFETs	Handout
October 01	Mon	CMOS Inverter VTC & ITC	5.1 - 5.4
October 03	Wed	PSPICE review	-
October 08	Mon	CMOS Inverter Noise Margin & Delay Model	5.5
October 10	Wed	CMOS Inverter Dynamic Power	5.6
October 15	Mon	CMOS Inverter Short Circuit Power	5.6
October 17	Wed	CMOS Inverter Leakage Power	5.7
October 22	Mon	Gate Sizing (Inverter Chain)	5.8
October 24	Wed	Interconnect Modeling I	4.1 - 4.2
October 29	Mon	Interconnect Modeling II	4.3 - 4.4
October 31	Wed	CMOS Fabrication	12.1 - 12.9
November 05	Mon	Design Rules & Basic Layout Techniques	11.1 - 11.6
November 07	Wed	Combinational Logic: NAND & NOR Gates	6.1 - 6.2
November 12	Mon	Combinational Logic: Transmission Gates	6.3
November 14	Wed	TEST	-
November 19	Mon	Logic Design Style: Static Logic	7.1
November 21	Wed	Logic Design Style: Dynamic & Damino Logics	7.2 - 7.3
November 26	Mon	Sequential Logic: D Flip-Flop	8.1 - 8.4
November 28	Wed	Timing Analysis	8.9
December 03	Mon	SRAM Memories	9.1 - 9.3
December 05	Wed	DRAM & FLASH Memories	9.4 - 9.6
December 10	Mon	Final Exam (5:30-7:30PM)	-

Example of a Digital Integrated Circuit?



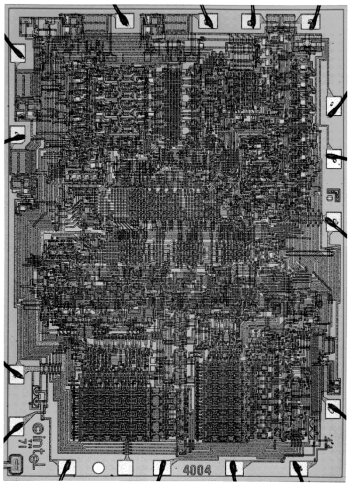
Introduction

Beginning of the Computer: ENIAC, the first electronic computer (1946)



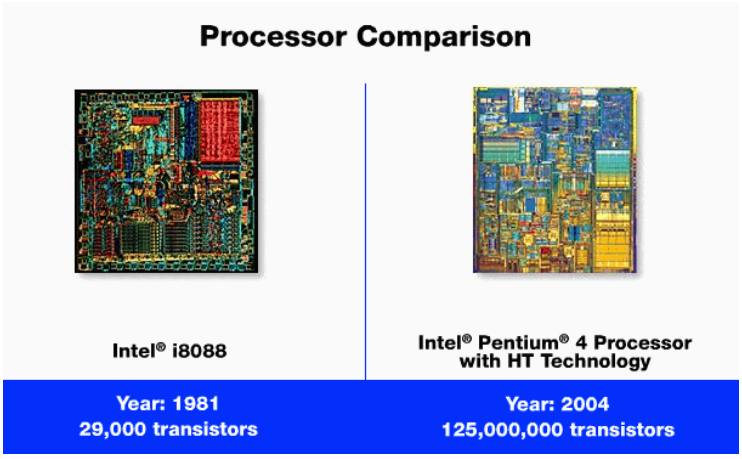
- 333 integer multiplication/second
- A six-week run was equivalent to 100 person-years of manual computation
- Program resides in the wired connections

Intel 4004 Microprocessor



- 1971
- 10 um NMOS-only
- 2300 transistors
- 1 MHz

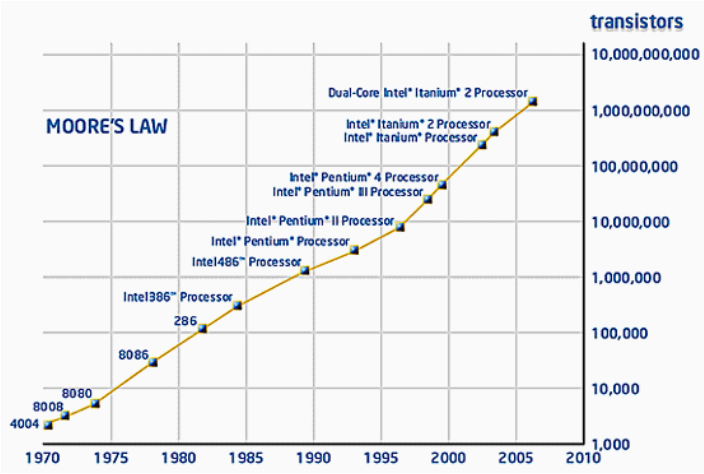
Intel Technology Advancement



Moor's Law

- In 1965, Gordon Moore (founder of Intel) had a very interesting observation. He noticed that the number of transistors on a chip doubled every 18 to 24 months.
- He made a prediction that semiconductor technology would double its effectiveness every 18 months.

Moor's Law for Intel Microprocessors



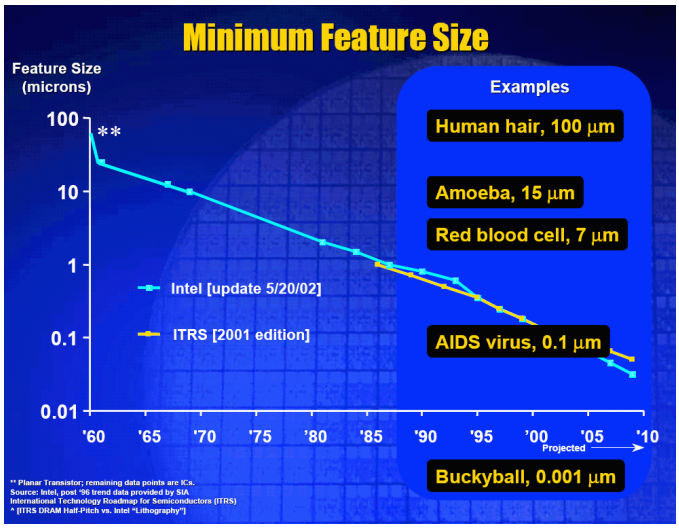
Source: www.intel.com

Moor's Law in Travel Industry

1978
Approximate Cost: $900
Approximate Travel Time: 7 hours

2003
Approximate Cost: 1¢
Approximate Travel Time: ¼ second

CMOS Scaling Scenario

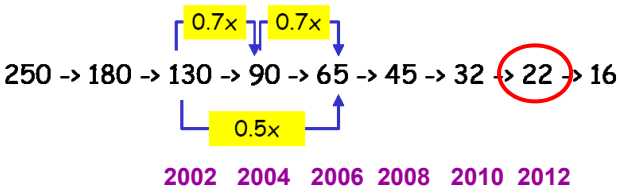


Why Scaling?

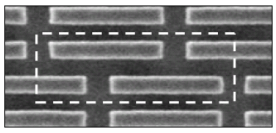
- What are the benefits of technology scaling?
- Why smaller device is better?

CMOS Scaling Calculation

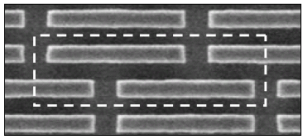
Scaling Calculator



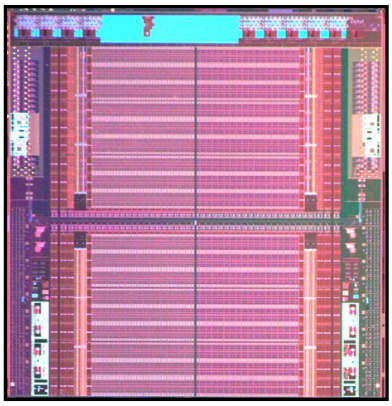
22nm SRAM Testchip (Intel)



0.092 um^2 SRAM cell
for high density applications

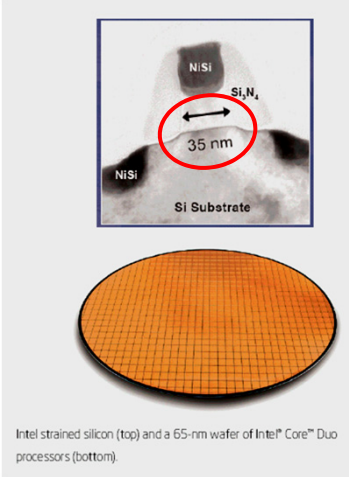


0.108 um^2 SRAM cell
for low voltage applications



10 million of these cells could fit in a square millimeter – about the size of the tip of a ballpoint pen

MOS in 65nm of Core Due Processor



Intel strained silicon (top) and a 65-nm wafer of Intel® Core™ Duo processors (bottom).

Distance between Si atoms = 5.43 ºA

No. of atoms in channel = 35 nm / 0.543 nm
= 64 Atoms!

Problem: Uncertainty in transistor behavior and difficult to control variation!

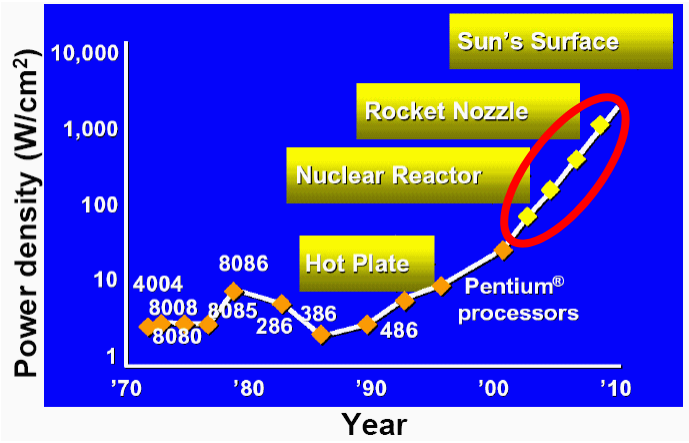
Benefit of Smaller Transistors

1) More transistors in the same foot-print
2) More functionality
3) Reduced cost per function
4) Faster devices and higher performance
5) Lower switching energy per transistor

Transistor Scaling Challenges

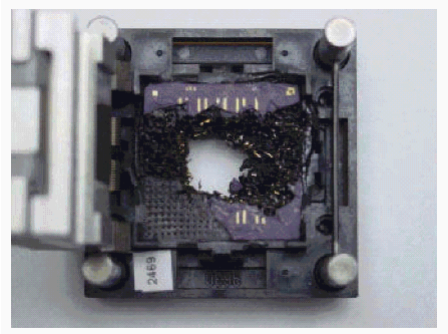
1) Feature sizes down to few atomic layers
2) Increase uncertainty of transistor behavior
3) Increase leakage power consumption
4) Difficult to maintain performance enhancement
5) Thermal limit issue

Power Density Problem

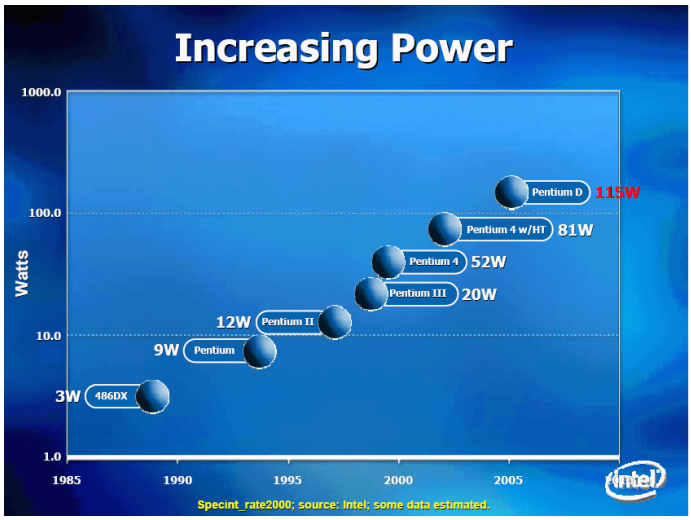


Power density too high to keep junction at low temperature.
Power reaching limits of air cooling.

Heat Management Consideration



Power Consumption Scenario



Some Calculations!

Power = 115 Watts

Supply Voltage = 1.2 V

Supply Current = 115 W / 1.2 V = 96 Amps!

Problem: Current density becomes a serious problem!

This is known as electromigration

Note: Fuses used for household appliances = 15 to 40 Amps

Another Calculations!

Power = 115 Watts

Chip Area = 2.2 Cm^2

Heat Flux = 115 W / 2.2 Cm^2 = 50 W/Cm^2 !

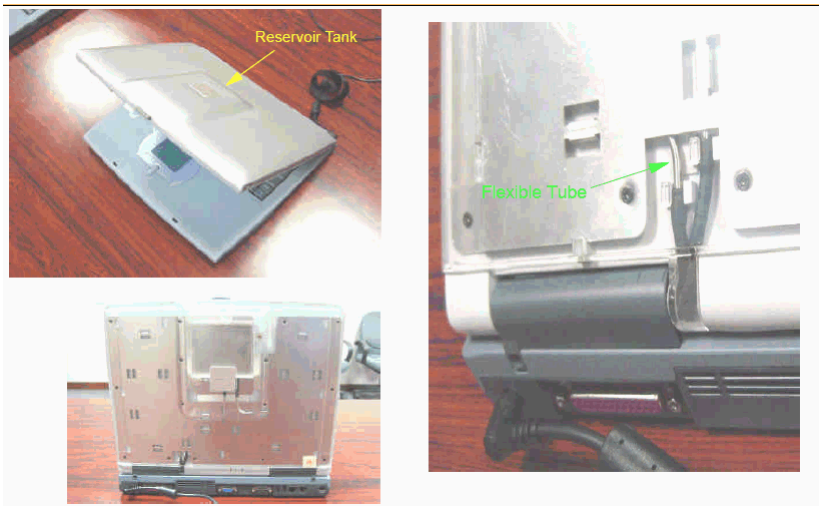
Problem: Heat flux is another serious issue!

Notes:
Heat flux in iron = 0.2 W/Cm^2
Heat flux in frying pan = 10 W/Cm^2

Method of Heat Management

1) **Proper heat removal system (expensive)**
2) **Improve manufacturing for low power MOS**
3) **Architectural solutions (multi-cores)**

Hitachi Water Cooling Laptop



Summary

Digital IC Business is Unique

- Things Get Better Every Few Years
- Companies Have to Stay on Moore's Law Curve to Survive

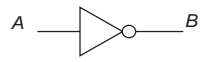
Benefits of Transistor Scaling

- Higher Frequencies of Operation
- Massive Functional Units, Increasing On-Die Memory
- Cost/Functionality Going Down

Downside of Transistor Scaling

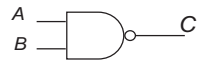
- Power (Dynamic and Static)
- Design and Manufacturing Cost

Basic Logic Gates



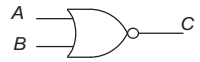
A	B
1	0
0	1

Inverter



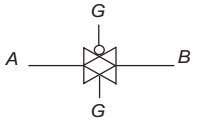
A	B	C
0	0	1
0	1	1
1	0	1
1	1	0

NAND



A	B	C
0	0	1
0	1	0
1	0	0
1	1	0

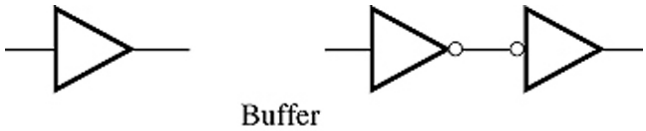
NOR



A	G	B
1	1	1
0	1	0
1	0	Z
0	0	Z

Transmission Gate

Alternative Gate Representation

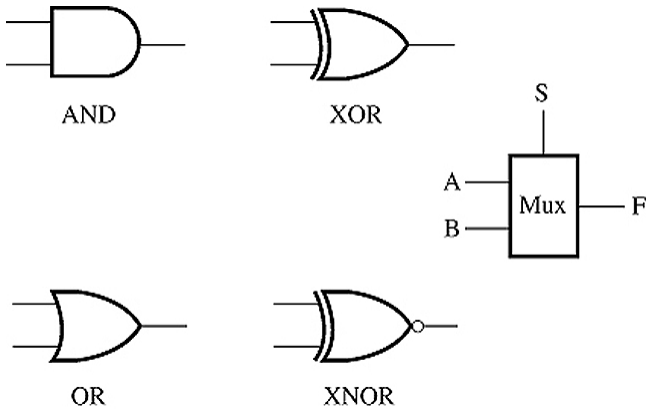


Buffer

3-input NOR

3-input NAND

Example 1: Use Basic Gates to Create Each



Review: DeMorgan's Theorem

1. Product terms (AND) in the original function transform to sum (OR) terms in the DeMorgan equivalence.
2. Sum (OR) terms in the original function transform to product (AND) terms in the DeMorgan equivalence.
3. All variables are inverted when transforming to and from a DeMorgan equivalence.
4. An overbar on the original function transforms to no overbar in the DeMorgan equivalence, and vice versa.

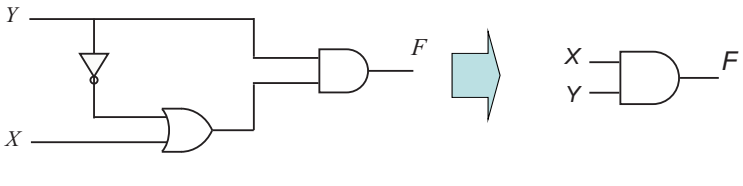
$$\overline{X+Y}=\overline{X}\,\overline{Y}$$

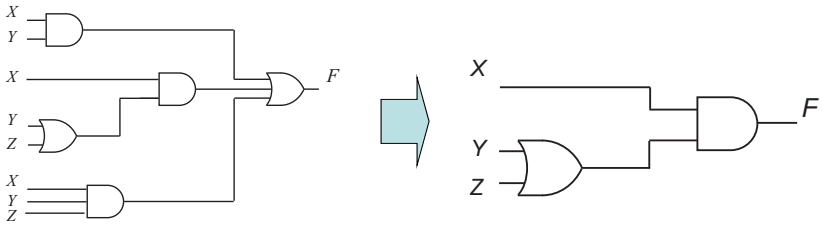
$$\overline{XY}=\overline{X}+\overline{Y}$$

Basic Boolean Properties

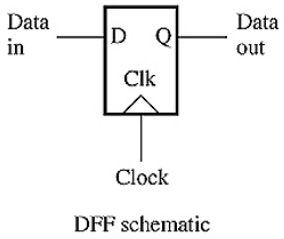
$X + Y = Y + X$	$XY = YX$
$X + 0 = X$	$X + 1 = 1$
$X0 = 0$	$X1 = X$
$X + X = X$	$XX = X$
$X\overline{X} = 0$	$X + \overline{X} = 1$
$(X + Y) + Z = X + (Y + Z)$	$(XY)Z = X(YZ)$
$X(Y + Z) = XY + XZ$	$X + (YZ) = (X + Y)(X + Z)$
$\overline{X + Y} = \overline{X}\,\overline{Y}$	$\overline{XY} = \overline{X} + \overline{Y}$

Example 2: Reduce to the Minimum Gates





Positive Edge D Flip-Flop

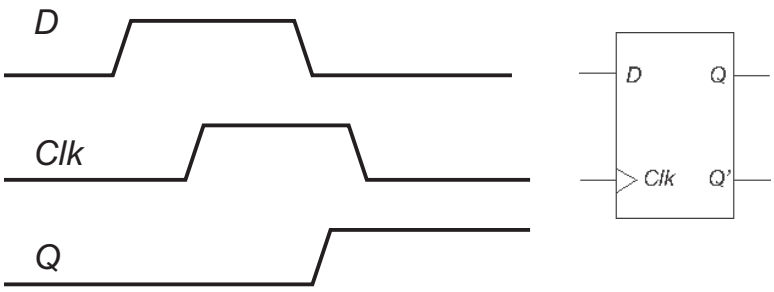


DFF schematic

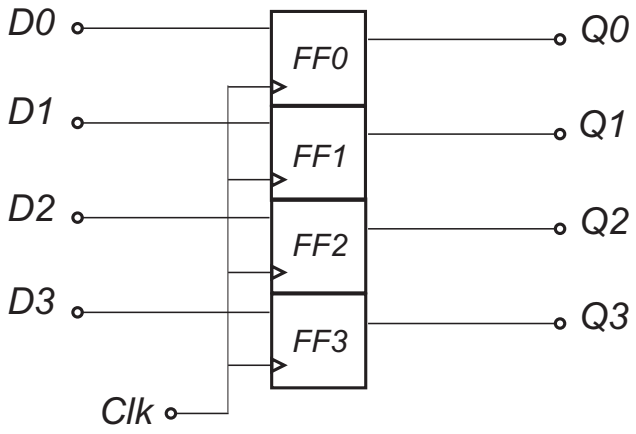
Clk	D	Q (old)	Q (new)
0	X	0	0
0	X	1	1
0→1	0	X	0
0→1	1	X	1
1	X	0	0
1	X	1	1
1→0	X	0	0
1→0	X	1	1

Excitation table

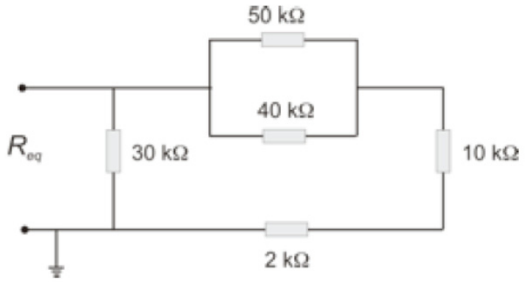
Timing in a D Flip-Flop



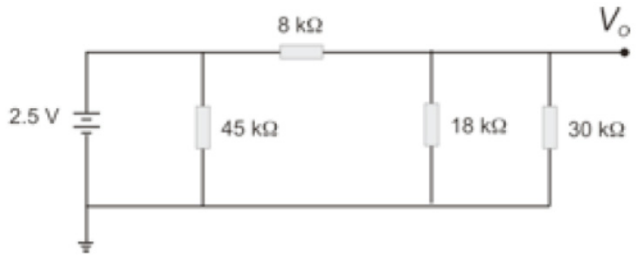
4-bit Register using D Flip-Flop



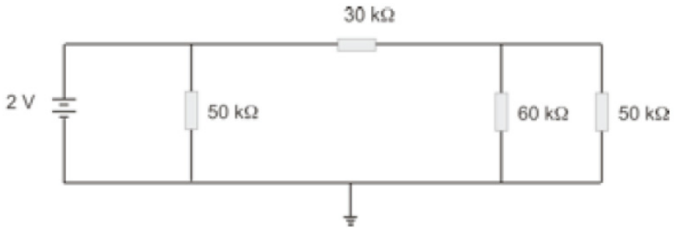
Review: Circuit Analysis – Find R_{eq}



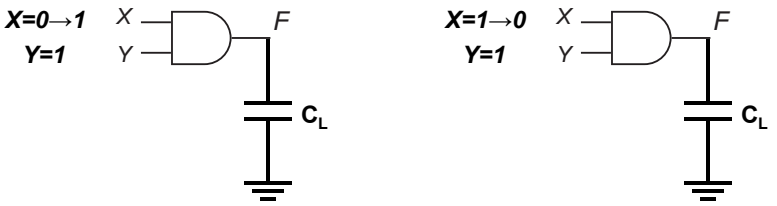
Review: Circuit Analysis – Thevenin Circuit



Review: Circuit Analysis – Power Calculation



Power Analysis for Logic Gates

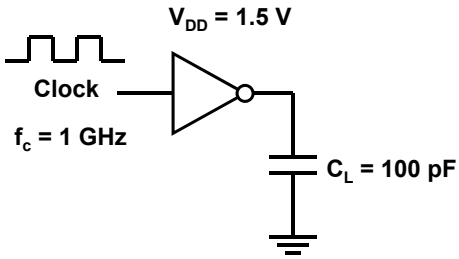


How much energy or power we consume for each transition?

Which element consumes energy?

Which element gets hot?

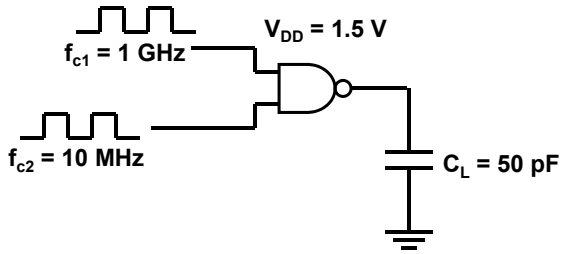
Example 1: Power and Energy Consumption



In this circuit:

1) Compute the power consumption in the inverter.
2) Compute the power consumption in the load capacitor.
3) How much energy stored in the load capacitor in each transition?
4) How much energy consumed in the inverter in each transition?

Example 2: Power Dissipation in Gated Clock



This circuit is typically used to “gate” the clock signal during sleep mode. Compute the average power dissipation in the above NAND gate.